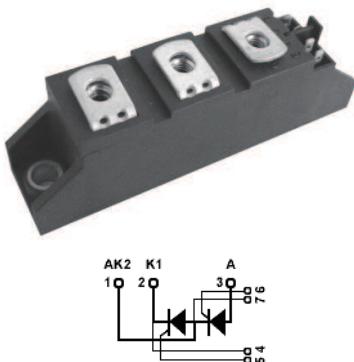


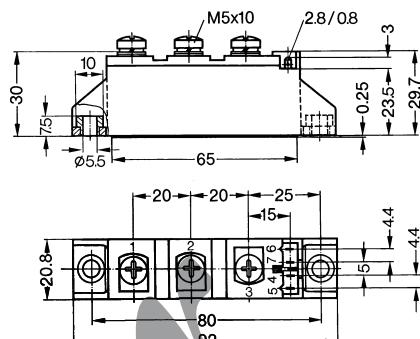
# STT100GKxx

## Thyristor-Thyristor Modules



Type	V <sub>RSM</sub> V <sub>DSM</sub>	V <sub>RRM</sub> V <sub>DRM</sub>
V	V	
STT100GK08	900	800
STT100GK12	1300	1200
STT100GK14	1500	1400
STT100GK16	1700	1600
STT100GK18	1900	1800
STT100GK20	2100	2000
STT100GK22	2300	2200

Tolerance: $\pm 0.5\text{mm}$   
Dimensions in mm (1mm=0.0394")



Symbol	Test Conditions	Maximum Ratings	Unit
I <sub>TRMS</sub> , I <sub>FRMS</sub> I <sub>TAVM</sub> , I <sub>FAVM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> T <sub>C</sub> =85°C; 180° sine	180 100	A
I <sub>TSM</sub> , I <sub>FSM</sub>	T <sub>VJ</sub> =45°C V <sub>R</sub> =0	1700 1800	A
	T <sub>VJ</sub> =T <sub>VJM</sub> V <sub>R</sub> =0	1540 1640	
$\int i^2 dt$	T <sub>VJ</sub> =45°C V <sub>R</sub> =0	14450 13500	A <sup>2</sup> s
	T <sub>VJ</sub> =T <sub>VJM</sub> V <sub>R</sub> =0	11850 11300	
(di/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> f=50Hz, t <sub>p</sub> =200us V <sub>D</sub> =2/3V <sub>DRM</sub> I <sub>G</sub> =0.45A dIg/dt=0.45A/us	150 500	A/us
	repetitive, I <sub>T</sub> =250A non repetitive, I <sub>T</sub> =I <sub>TAVM</sub>		
(dv/dt) <sub>cr</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> ; V <sub>DR</sub> =2/3V <sub>DRM</sub> R <sub>GK</sub> = $\infty$ ; method 1 (linear voltage rise)	1000	V/us
P <sub>GM</sub>	T <sub>VJ</sub> =T <sub>VJM</sub> I <sub>T</sub> =I <sub>TAVM</sub>	10 5	W
P <sub>GAV</sub>		0.5	W
V <sub>RGM</sub>		10	V
T <sub>VJ</sub> T <sub>VJM</sub> T <sub>stg</sub>		-40...+125 125 -40...+125	°C
V <sub>ISOL</sub>	50/60Hz, RMS I <sub>ISOL</sub> $\leq$ 1mA	3000 3600	V~
M <sub>d</sub>	Mounting torque (M5) Terminal connection torque (M5)	2.5-4.0/22-35 2.5-4.0/22-35	Nm/lb.in.
Weight	Typ.	81	g

Sirec<sup>®</sup>rectifier

# STT100GKxx

## Thyristor-Thyristor Modules

Symbol	Test Conditions	Characteristic Values	Unit
$I_{RRM}, I_{DRM}$	$V_{VJ}=V_{VJM}; V_R=V_{RRM}; V_D=V_{DRM}$	15	mA
$V_T, V_F$	$I_T, I_F=300A; T_{VJ}=25^\circ C$	1.74	V
$V_{TO}$	For power-loss calculations only ( $T_{VJ}=T_{VJM}$ )	0.85	V
$r_T$		3.2	$m\Omega$
$V_{GT}$	$V_D=6V; T_{VJ}=25^\circ C$ $T_{VJ}=-40^\circ C$	1.5 1.6	V
$I_{GT}$	$V_D=6V; T_{VJ}=25^\circ C$ $T_{VJ}=-40^\circ C$	100 200	mA
$V_{GD}$	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	0.25	V
$I_{GD}$	$T_{VJ}=T_{VJM}; V_D=2/3V_{DRM}$	10	mA
$I_L$	$T_{VJ}=25^\circ C; t_p=30\mu s; V_D=6V$ $I_G=0.45A; dI/dt=0.45A/\mu s$	200	mA
$I_H$	$T_{VJ}=25^\circ C; V_D=6V; R_{GK}=\infty$	150	mA
$t_{gd}$	$T_{VJ}=25^\circ C; V_D=1/2V_{DRM}$ $I_G=0.45A; dI/dt=0.45A/\mu s$	2	us
$t_q$	$T_{VJ}=T_{VJM}; I_T=150A; t_p=200\mu s; -dI/dt=10A/\mu s$ $V_R=100V; dv/dt=20V/\mu s; V_D=2/3V_{DRM}$	typ. 185	us
$Q_s$		170	uC
$I_{RM}$	$T_{VJ}=T_{VJM}; I_T=50A; -dI/dt=6A/\mu s$	45	A
$R_{thJC}$	per thyristor/diode; DC current per module	0.22 0.11	K/W
$R_{thJK}$	per thyristor/diode; DC current per module	0.42 0.21	K/W
$ds$	Creeping distance on surface	12.7	mm
$da$	Creepage distance in air	9.6	mm
$a$	Maximum allowable acceleration	50	$m/s^2$

### FEATURES

- \* International standard package
- \* DCB base plate
- \* Glass passivated chips
- \* Isolation voltage 3600 V~
- \* UL file NO.310749
- \* RoHs compliant

### APPLICATIONS

- \* DC motor control
- \* Softstart AC motor controller
- \* Light, heat and temperature control

### ADVANTAGES

- \* Space and weight savings
- \* Simple mounting with two screws
- \* Improved temperature and power cycling
- \* Reduced protection circuits

**Sirecifier®**

# STT100GKxx

## Thyristor-Thyristor Modules

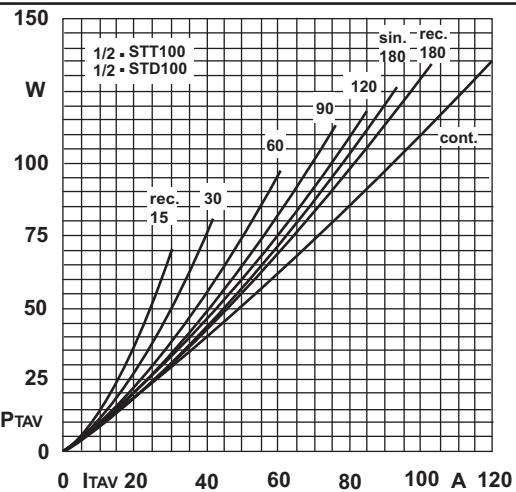


Fig.1L Power dissipation per thyristor vs. on-state current

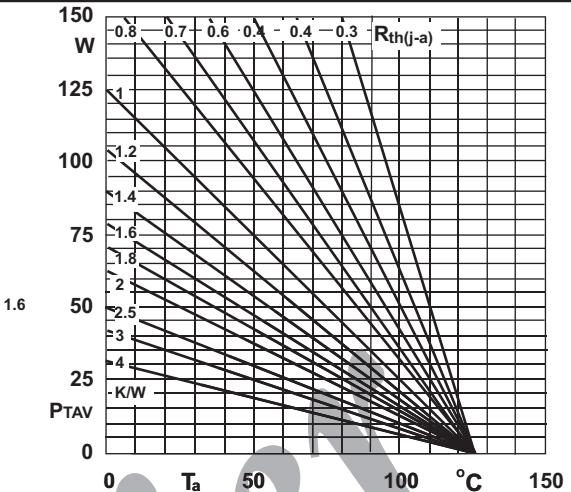


Fig.1R Power dissipation per thyristor vs. ambient temp

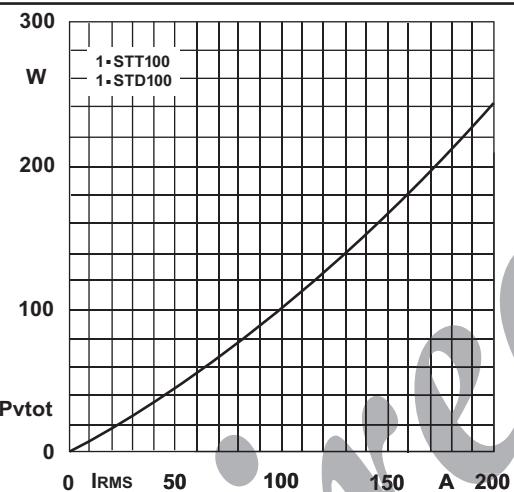


Fig.2L Power dissipation per module vs. rms current

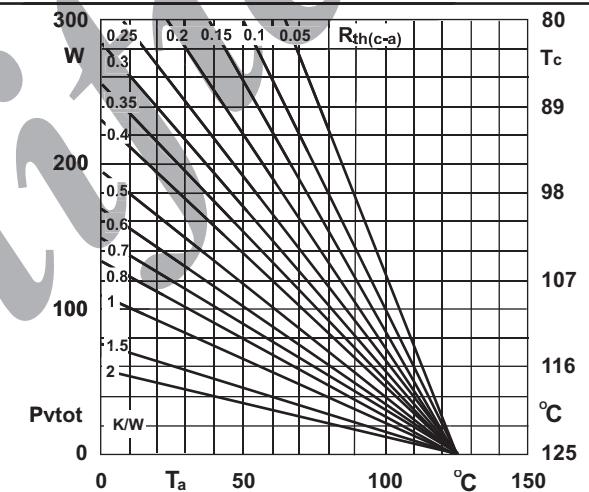


Fig.2R Power dissipation per module vs. case temp

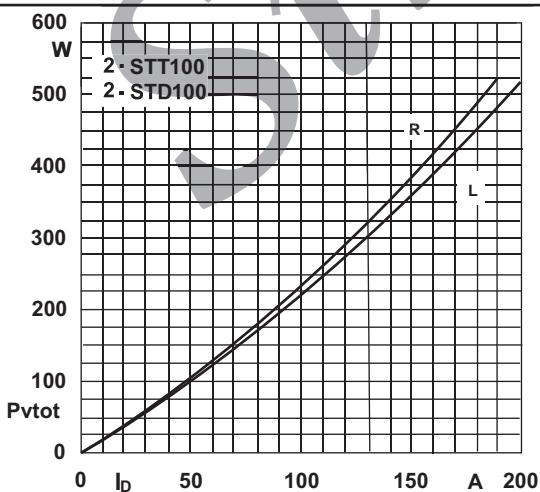


Fig.3L Power dissipation of two modules vs. direct current

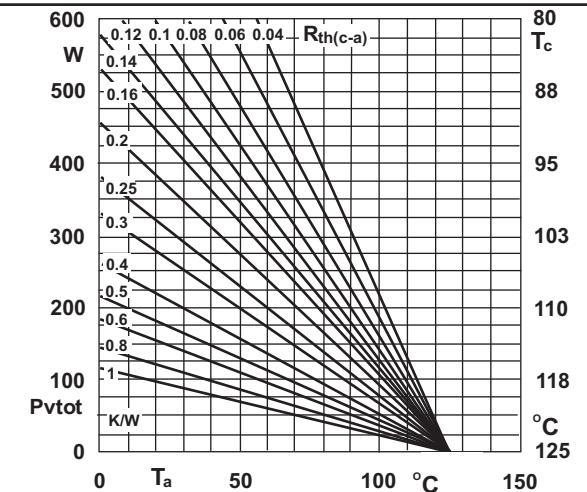


Fig.3R Power dissipation of two modules vs. case temp

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# STT100GKxx

## Thyristor-Thyristor Modules

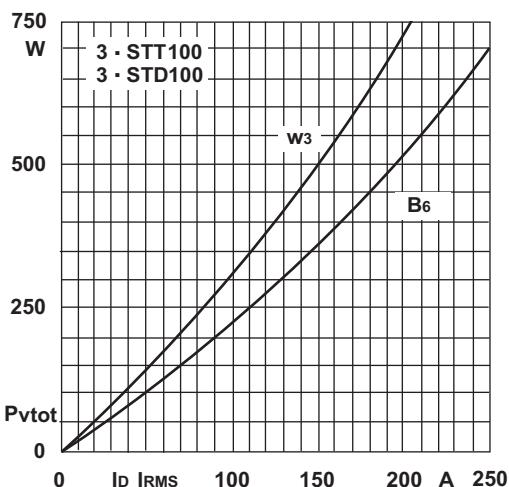


Fig.4L Power dissipation of three modules vs. direct and rms current

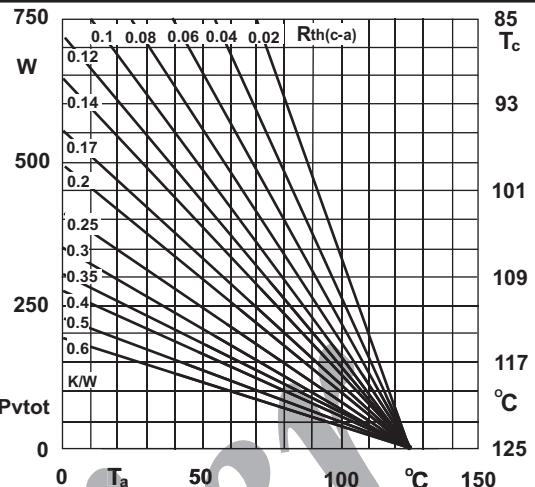


Fig.4R Power dissipation of three modules vs. case temp

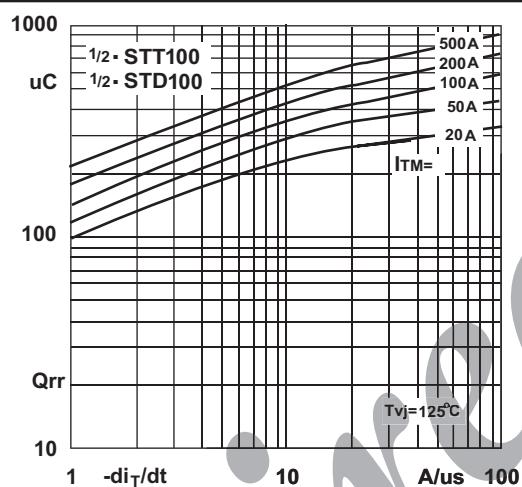


Fig.5 Recovered charge vs. current decrease

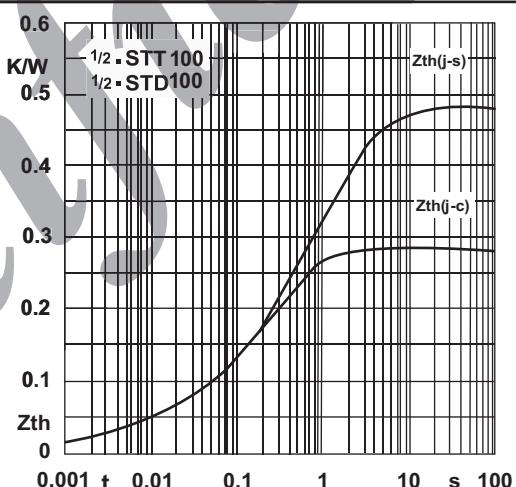


Fig.6 Transient thermal impedance vs. time

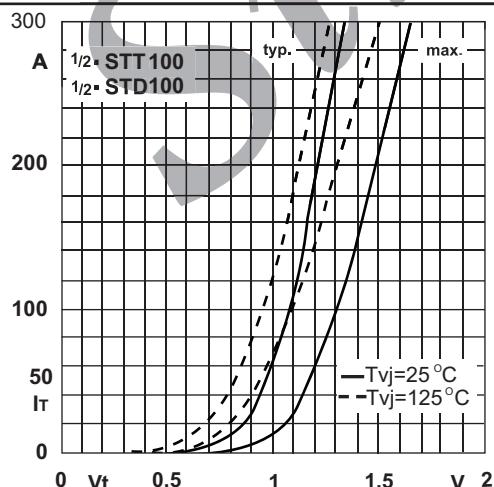


Fig.7 On-state characteristics

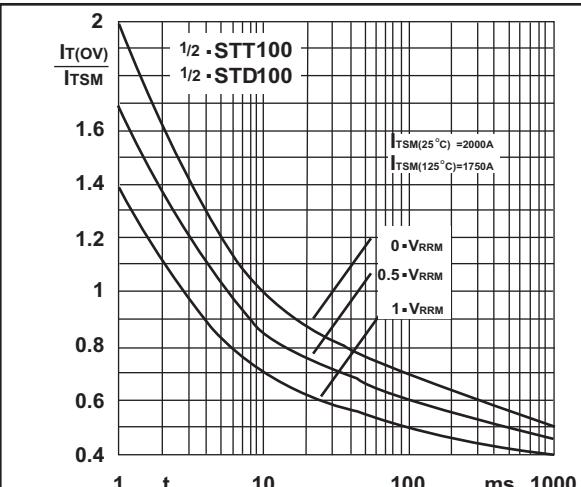


Fig.8 Surge overload current vs. time

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